

Amendments to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

Listing of Claims:

1. (Currently amended) A light emitting device comprising:  
a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element and a light emitting element, the light emitting element comprising a light emitting layer including an organic compound; and  
a plurality of source signal lines for supplying signals to the switching element,  
wherein at least one of the plurality of source signal lines comprises a first conductor and a first plated film on upper and side surfaces of the first conductor, and  
wherein said first conductor comprises an Ag particle.
2. (Previously presented) A light emitting device according to claim 1, wherein the plated film is formed by an electroplating method.
3. (Previously presented) A light emitting device according to claim 1, wherein the plated film comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.
4. (Previously presented) A light emitting device according to any one of claims 1, wherein the first conductor is made of the same material as a gate electrode of the switching element.
5. (Original) A light emitting device according to claim 1, wherein the switching element comprises at least one thin film transistor.

6. (Original) An electronic appliance comprising the light emitting device according to claim 1, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

7. (Currently amended) A light emitting device comprising:  
a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element and a light emitting element, the light emitting element comprising a light emitting layer including an organic compound; and  
a plurality of power supply lines for supplying potentials to the light emitting element, wherein at least one of the plurality of power supply lines comprises a first conductor and a first plated film on upper and side surfaces of the first conductor, and  
wherein said first conductor comprises an Ag particle.

8. (Previously presented) A light emitting device according to claim 7, wherein the plated film is formed by an electroplating method.

9. (Previously presented) A light emitting device according to claim 7, wherein the plated film comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

10. (Previously presented) A light emitting device according to any one of claims 7, wherein the first conductor is made of the same material as a gate electrode of the switching element.

11. (Original) A light emitting device according to claim 7, wherein the switching element comprises at least one thin film transistor.

12. (Original) An electronic appliance comprising the light emitting device according to claim 7, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

13. (Currently amended) A light emitting device comprising:  
a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element and a light emitting element, the light emitting element comprising a light emitting layer including an organic compound;  
a plurality of source signal lines for supplying signals to the switching element; and  
a plurality of power supply lines for supplying potentials to the light emitting element,  
wherein at least one of the plurality of source signal lines comprises a first conductor and a first plated film on upper and side surfaces of the first conductor, **[[and]]**  
wherein at least one of the plurality of power supply lines comprises a second conductor and a second plated film on upper and side surfaces of the second conductor, and  
wherein each of said first conductor and said second conductor comprises an Ag particle.

14. (Previously presented) A light emitting device according to claim 13, wherein at least one of the first plated film and the second plated film is formed by an electroplating method.

15. (Previously presented) A light emitting device according to claim 13, wherein at least one of the first plated film and the second plated film comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

16. (Original) A light emitting device according to claim 13, wherein the first conductor and the second conductor are simultaneously formed.

17. (Previously presented) A light emitting device according to claim 13, wherein at least one of the first plated film and the second plated film is made of the same material as a gate electrode of the switching element.

18. (Previously presented) A light emitting device according to any one of claims 13, wherein at least one of the first plated film and the second plated film is formed by a printing method.

19. (Original) A light emitting device according to claim 13, wherein the switching element comprises at least one thin film transistor.

20. (Original) An electronic appliance comprising the light emitting device according to claim 13, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

21. (Withdrawn) A light emitting device comprising:  
a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element and a light emitting element;  
a plurality of source signal lines for supplying signals to the switching element; and  
at least one terminal,  
wherein at least one of the plurality of source signal lines comprises a first conductor and a first conductive coating on the first conductor, and  
wherein the terminal comprises a second conductor and a second conductive coating on the second conductor.

22. (Withdrawn) A light emitting device according to claim 21, wherein at least one of the first conductive coating and the third conductive coating is formed by an electroplating method.

23. (Withdrawn) A light emitting device according to claim 21, wherein at least one of the first and second conductive coating comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

24. (Withdrawn) A light emitting device according to claim 21, wherein the first conductor and the second conductor are simultaneously formed.

25. (Withdrawn) A light emitting device according to claim 21, wherein at least one of the first conductive coating and the second conductive coating is made of the same material as a gate electrode of the switching element.

26. (Withdrawn) A light emitting device according to claim 21, wherein at least one of the first conductive coating and the second conductive coating is formed by a printing method.

27. (Withdrawn) A light emitting device according to claim 21, wherein the switching element comprises at least one thin film transistor.

28. (Withdrawn) An electronic appliance comprising the light emitting device according to claim 21, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

29. (Withdrawn) A light emitting device comprising:  
a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element and a light emitting element;  
a plurality of power supply lines for supplying potentials to the light emitting element;  
and

at least one terminal electrically connected to the plurality of power supply lines wherein at least one of the plurality of power supply lines comprises a first conductor and a first conductive coating on the first conductor, and

wherein the terminal comprises a second conductor and a second conductive coating on the second conductor.

30. (Withdrawn) A light emitting device according to claim 29, wherein at least one of the first conductive coating and the second conductive coating is formed by an electroplating method.

31. (Withdrawn) A light emitting device according to claim 29, wherein at least one of the first conductive coating and the second conductive coating comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

32. (Withdrawn) A light emitting device according to claim 29, wherein the first conductor and the second conductor are simultaneously formed.

33. (Withdrawn) A light emitting device according to claim 29, wherein at least one of the first conductive coating and the second conductive coating is made of the same material as a gate electrode of the switching element.

34. (Withdrawn) A light emitting device according to claim 29, wherein at least one of the first conductive coating and the second conductive coating is formed by a printing method.

35. (Withdrawn) A light emitting device according to claim 29, wherein the switching element comprises at least one thin film transistor.

36. (Withdrawn) An electronic appliance comprising the light emitting device according to claim 29, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

37. (Withdrawn) A light emitting device comprising:  
a pixel portion comprising a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a first switching element, a plurality of source signal lines for supplying signals to the switching element, and a light emitting element; and  
a driver circuit for driving the plurality of pixels, the driver circuit having a second switching element and a third switching element,  
wherein at least one of the plurality of source signal lines comprises a conductor and a conductive coating on the conductor.

38. (Withdrawn) A light emitting device according to claim 37, wherein the first, second, and third switching elements are n-channel thin film transistors.

39. (Withdrawn) A light emitting device according to claim 37, wherein the first, second, and third switching elements are p-channel thin film transistors.

40. (Withdrawn) A light emitting device according to claim 37, wherein the second and third switching elements compose at least one of an EEMOS circuit and an EDMOS circuit.

41. (Withdrawn) A light emitting device according to claim 37, wherein the second switching element is an n-channel thin film transistor and the third switching element is a p-channel thin film transistor.

42. (Withdrawn) A light emitting device according to claim 37, wherein the conductive coating is formed by an electroplating method.

43. (Withdrawn) A light emitting device according to claim 37, wherein the conductive coating is formed by a printing method.

44. (Withdrawn) A light emitting device according to claim 37, wherein the conductive coating comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

45. (Withdrawn) A light emitting device according to claim 37, wherein the conductor is made of the same material as a gate electrode of the first, second, and third switching element.

46. (Withdrawn) A light emitting device according to claim 37, wherein at least one of the first, second, and third switching element comprises at least one thin film transistor.

47. (Withdrawn) A light emitting device according to claim 37, wherein the first switching element comprises a plurality of channel forming regions.

48. (Withdrawn) A light emitting device according to claim 37, wherein the first switching element comprises three channel forming regions.

49. (Withdrawn) A light emitting device according to claim 37, wherein at least one of the first, second and third switching elements comprises a gate electrode having a taper portion, a channel forming region overlapped with the gate electrode, and an impurity region partially overlapped with the gate electrode.

50. (Withdrawn) A light emitting device according to claim 49, wherein the impurity region in at least one of the first, second, and third switching elements comprises a region having



a concentration gradient at least at an impurity concentration of  $1 \times 10^{17}$  to  $1 \times 10^{18} / \text{cm}^3$ , and the impurity concentration is increased as a distance from the channel forming region increases.

51. (Withdrawn) An electronic appliance comprising the light emitting device according to claim 37, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

52. (Withdrawn) A light emitting device comprising:  
a pixel portion comprising a plurality of pixels arranged in a matrix, each of the plurality of pixels comprising a switching element, a light emitting element, and a plurality of power supply lines for supplying potentials to the light emitting element; and  
a driver circuit for driving the plurality of pixels, the driver circuit having a second switching element and a third switching element,  
wherein at least one of the plurality of power supply lines comprises a conductor and a conductive coating on the conductor.

53. (Withdrawn) A light emitting device according to claim 52, wherein at least one of the first, second, and third switching element comprises at least one thin film transistor.

54. (Withdrawn) A light emitting device according to claim 52, wherein the first, second, and third switching elements are n-channel thin film transistors.

55. (Withdrawn) A light emitting device according to claim 52, wherein the first, second, and third switching elements are p-channel thin film transistors.

56. (Withdrawn) A light emitting device according to claim 52, wherein the second and third switching elements compose at least one of an EEMOS circuit and an EDMOS circuit.

57. (Withdrawn) A light emitting device according to claim 52, wherein the second switching element is an n-channel thin film transistor and the third switching element is a p-channel thin film transistor.

58. (Withdrawn) A light emitting device according to claim 52, wherein the conductive coating is formed by an electroplating method.

59. (Withdrawn) A light emitting device according to claim 52, wherein the conductive coating is formed by a printing method.

60. (Withdrawn) A light emitting device according to claim 52, wherein the conductive coating comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

61. (Withdrawn) A light emitting device according to claim 52, wherein the conductor is made of the same material as a gate electrode of the switching element.

62. (Withdrawn) A light emitting device according to claim 52, wherein the first switching element comprises a plurality of channel forming regions.

63. (Withdrawn) A light emitting device according to claims 52, wherein the first switching element comprises three channel forming regions.

64. (Withdrawn) A light emitting device according to claim 52, wherein at least one of the first, second and third switching elements comprises a gate electrode having a taper portion, a channel forming region overlapped with the gate electrode, and an impurity region partially overlapped with the gate electrode.

65. (Withdrawn) A light emitting device according to claim 64, wherein the impurity region in at least one of the first, second, and third switching elements comprises a region having a concentration gradient at least at an impurity concentration of  $1 \times 10^{17}$  to  $1 \times 10^{18} / \text{cm}^3$ , and the impurity concentration is increased as a distance from the channel forming region increases.

66. (Withdrawn) An electronic appliance comprising the light emitting device according to claim 52, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

67-76. (Canceled)

77. (Withdrawn) A light emitting device according to claim 1, wherein the device further comprises at least one terminal, and the terminal comprises a second conductor and a second conductive coating on the second conductor.

78. (Withdrawn) A light emitting device according to claim 7, wherein the device further comprises at least one terminal, and the terminal comprises a second conductor and a second conductive coating on the second conductor.

79. (New) A light emitting device comprising:  
at least a thin film transistor formed over a substrate;  
a wiring formed over the substrate, the wiring comprising a conductor and a plated film on upper and side surfaces of the conductor,  
an interlayer insulating film formed over the thin film transistor and the wiring; and  
a light emitting element formed over the interlayer insulating film, the light emitting element electrically connected to the thin film transistor,  
wherein said first conductor comprises an Ag particle, and

wherein the thin film transistor and the wiring are electrically connected to each other through a contact hole formed in the interlayer insulating film.

80. (New) A light emitting device according to claim 79, wherein the plated film is formed by an electroplating method.

81. (New) A light emitting device according to claim 79, wherein the plated film comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

82. (New) An electronic appliance comprising the light emitting device according to claim 79, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.

83. (New) A light emitting device comprising:  
at least a thin film transistor formed over a substrate;  
a source signal line formed over the substrate, the source signal line comprising a conductor and a plated film on upper and side surfaces of the conductor,  
an interlayer insulating film formed over the thin film transistor and the source signal line; and  
a light emitting element formed over the interlayer insulating film, the light emitting element electrically connected to the thin film transistor,  
wherein said first conductor comprises an Ag particle,  
wherein the thin film transistor and the wiring are electrically connected to each other through a contact hole formed in the interlayer insulating film, and  
wherein a gate electrode of the thin film transistor and the source signal line are formed on a same insulating film.

84. (New) A light emitting device according to claim 83, wherein the plated film is formed by an electroplating method.

85. (New) A light emitting device according to claim 83, wherein the plated film comprises at least one selected from the group consisting of Cu, Al, Au, Ag, and an alloy thereof as a main component.

86. (New) An electronic appliance comprising the light emitting device according to claim 83, wherein the light emitting device is selected from the group consisting of an electroluminescence display device, a personal computer, and a digital versatile disk.